

Diode Chip

DTHP 09-065

tentative

Circuit Diagram



Product Summary

Characteristics	Value	Unit	
V_{RRM}	650	V	
I F _(AV)	22	Α	
Chip Dimensions	3,6x2,5	mm	
unsawn wafer	Contact Bare Die Sales		
sawn on foil	Yes		
in waffle pack	Yes		

Applications

- antiparallel diode for high frequency switching
- antisaturation diode
- snubber diode
- freewheeling diode in converters & motor control
- rectifiers in switch mode power supplies (SMPS)
- inductive heating & melting
- uninterruptible power supplies (UPS)
- ultrasonic cleaners & welders

Features

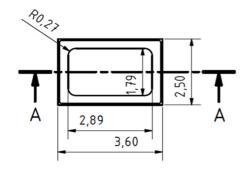
- fast, soft SONIC diode
- low forward voltage drop
- small temp. Coefficient
- low switching losses
- high ruggedness
- anode top
- Tvjm = 175°C

Mechanical Characteristic

Characteristic		Conditions	Value	Unit
Area active			5,38	mm²
Area total			9,00	mm²
Thickness			70	μm
Wafer size Ø			150	mm
Die Per Wafer			1624	
Material			Si	
Passivation front side			SiN	
Metalisation front side		bondable:	Al	
Metalisation back side		solderable (only):	Al/Ti/NiV/Ag	
Recom. wire bonds (AI)	Anode	Number	3	
*= stitch bonds		Ø	300	μm
Reject ink dot size		Ø	0.4 - 1.0	mm
Recom. solder temp.			<300	°C
Recom. Storage environment	sawn on foil	in org. container, in dry nitrogen	<6	month
	unsawn wafer	in org. container, in dry nitrogen	<2	year
	in waffle pack	in org. container, in dry nitrogen	<2	year
Storage temp.			-4040	°C

Dimensions

All dimensions in mm



Passivation Anode (metal)

Cathode (metal)

IXYS reserves the right to change limits, conditions and dimensions

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Electrical Parameters

Symbol	Conditions		Value			
		Min	Тур	Max	Unit	
Static Characterist						
I _R	V = V _{RRM}	Tvj = 25°C			20	μA
		Tvj = 150°C		0,2		mA
V_F	If = 25A	Tvj = 25°C		1,40	1,60	V
		Tvj = 150°C		1,35		V
V_{F0}	For power loss calculations only				1	V
r_F		Tvj = 175°C			20,0	mΩ
T _{VJ}			-55		175	°C
<i>I_{F(AV)}</i> *	DC	Tc = 80°C		22		Α
I _{FSM} *	V = 0V	Tvj = 45°C			100	Α
R +h IC *	DC current				3	K/W

Dynamic Characteristics

Q_{rr}			-	μC
I _{RM}	V = 300V	Tvj = 25°C	-	Α
t _{rr}	If = 25A	$dIf/dt = 800A/\mu s$	-	ns
E _{rec}			-	mJ
Q _{rr}			2	μC
I _{RM}	V = 300V	Tvj = 150°C	26	Α
t _{rr}	If = 25A	$dIf/dt = 800A/\mu s$	150	ns
E _{rec}			0,35	mJ

^{*} Data according to assembled 380 μ m DCB

Data according to IEC 60747

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Should you intend to use the product in aviation applications, in life or health endangering or life support applications, please notify. For any such applications we urgently recommend

- to perform joint risks and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures to ensure application specific product capabilities and notify that IXYS may deliver dependant on the realisation of any such measures.

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